

Title (en)  
ENHANCED STRUCTURE AND METHOD FOR BURIED LOCAL INTERCONNECTS

Title (de)  
ERWEITERTE STRUKTUR UND VERFAHREN FÜR VERGRABENE LOKALE VERBINDUNGEN

Title (fr)  
STRUCTURE ET PROCEDE AMELIORES POUR FORMER DES INTERCONNEXIONS LOCALES ENTERREES

Publication  
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Application  
**EP 02734808 A 20020614**

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Abstract (en)  
[origin: WO03107430A1] A structure and method is disclosed for forming a buried interconnect (10) of an integrated circuit in a single crystal semiconductor layer (12) of a substrate. The buried interconnect is formed of a deposited conductor and has one or more vertical sidewalls (18) which contact a single crystal region of an electronic device (20) formed in the single crystal semiconductor layer.

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See references of WO 03107430A1

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